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	Applicant: Leonard Forbes	
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## U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
MP	4,394,181	07/19/1983	Nicholas, K.H.	148	1.5	09/28/81
MP	5,145,794	09/08/1992	Kase, M., et al.	437	24	09/06/90
MP	5,254,484	10/19/1993	Hefner, H., et al.	437	24	09/24/91
MP	5,298,435	03/29/1994	Aronowitz, S., et al.	437	24	09/03/92
MP	5,312,766	05/17/1994	Aronowitz, S., et al.	437	24	02/07/92
MP	5,426,069	06/20/1995	Selvakumar, C.R., et al.	437	131	04/09/92

## FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes	No

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

MP	Berti, M., et al., "Composition and Structure of Si-Ge Layers Produced by Ion Implantation and Laser Melting", <u>J. Mater. Res.</u> , Vol. 6, No. 10, pp. 2120-2126, (1991) <u>10/91</u>
MP	Berti, M., et al., "Laser Induced Epitaxial Regrowth of Si <sub>1-x</sub> Gex/Si Layers Produced by Ge Ion Implantation", <u>Appl. Surf. Sci.</u> , Vol. 43, pp. 158-164, (1989) <u>1/89</u>
MP	Chilton, B.T., et al., "Solid Phase Epitaxial Regrowth of Strained Si <sub>1-x</sub> Gex/Si Strained-layer Structures Amorphized by Ion Implantation", <u>Appl. Phys. Lett.</u> , Vol. 54, No. 1, pp. 42-44, (1989) <u>1/89</u>
MP	Myerson, B.S., et al., "SiGe-Channel Heterojunction p-MOSFET's", <u>IEEE Trans. on Electron Devices</u> , Vol. ED-41, No. 1, pp. 90-100, (Jan. 1994)
MP	Paine, D.C., et al., "The Growth of Strained Si <sub>1-x</sub> Gex Alloys on (100) Silicon Using Solid Phase Epitaxy", <u>J. Mater. Res.</u> , Vol. 5, No., pp. 1023-1031, (1990) <u>5/90</u>
MP	People, R., et al., "Calculation of critical layer thickness versus lattice mismatch for GexSi <sub>1-x</sub> /Si strained-layer heterostructures", <u>Appl. Phys. Lett.</u> , Erratum, 47, 322, (1985) <u>8/85</u>
MP	Reedy, R., et al., "High Quality CMOS in Thin (100nm) Silicon on Sapphire", <u>IEEE Elect. Device Lett.</u> , Vol. 9, No. 1, pp 32-34, (Jan. 1988)
MP	Wang, K.L., et al., "High Performance GeSi Quantum-Well PMOS on SIMOX", <u>Proc. Int. Electron Device Meeting</u> , San Francisco, pp. 777-778, (Dec. 1992)

Examiner <u>Prenty</u>	Date Considered <u>10/98</u>
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\*Substitute Disclosure Statement Form (PTO-1449)

\*\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.